



BUK761R7-40E

N-channel TrenchMOS standard level FET

19 May 2016

Product data sheet

1. General description

Standard level N-channel MOSFET in a SOT404A package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with $V_{GS(th)}$ rating of greater than 1 V at 175 °C

3. Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	-	40	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	[1]	-	-	120	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1		-	-	324	W
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11		-	1.32	1.6	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$I_D = 25\text{ A}$; $V_{DS} = 32\text{ V}$; $V_{GS} = 10\text{ V}$; Fig. 13 ; Fig. 14		-	34.7	-	nC

[1] Continuous current is limited by package.

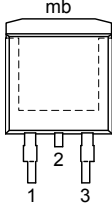
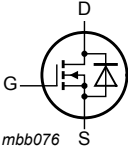


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 D2PAK (SOT404A)	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK761R7-40E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404A

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK761R7-40E	BUK761R7-40E

8. Limiting values

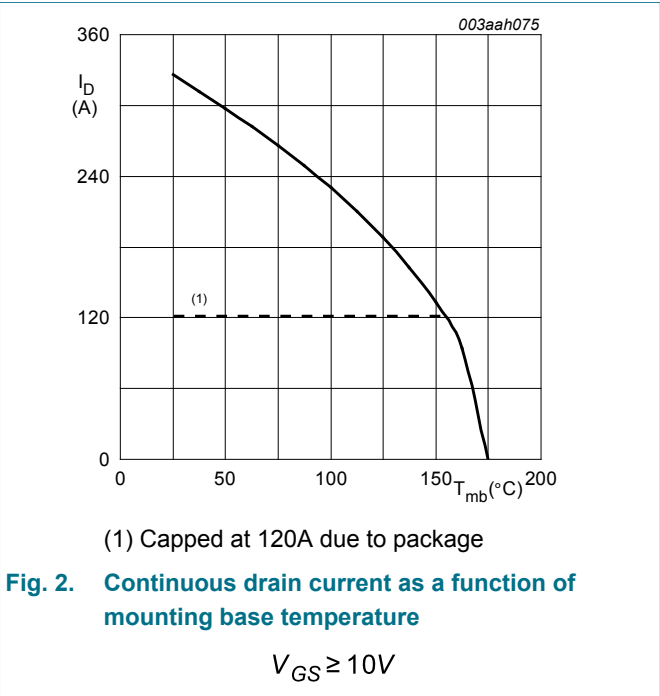
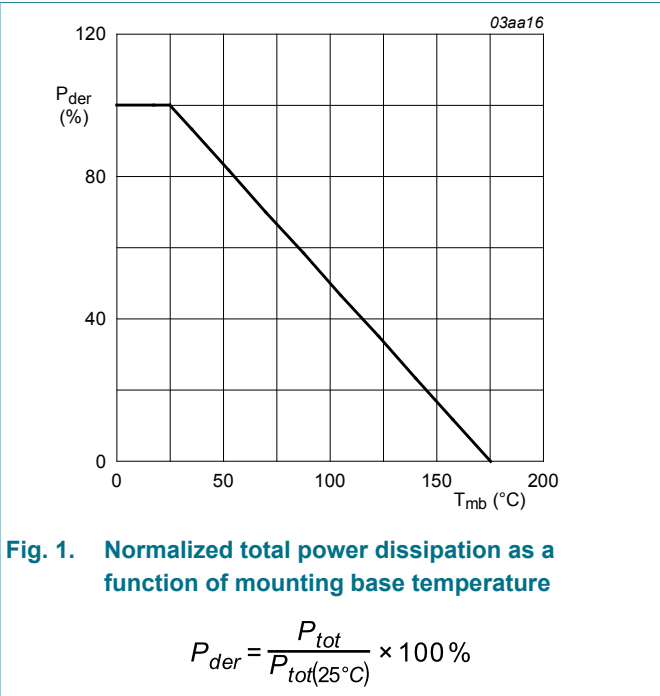
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	40	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$		-	40	V
V_{GS}	gate-source voltage	DC; $T_j \leq 175\text{ °C}$		-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1		-	324	W
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	[1]	-	120	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; Fig. 2		-	120	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 3		-	1306	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I _S	source current	T _{mb} = 25 °C	[1]	-	120	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	1306	A
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 120 A; V _{sup} ≤ 40 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; Fig. 4	[2][3]	-	801	mJ

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.



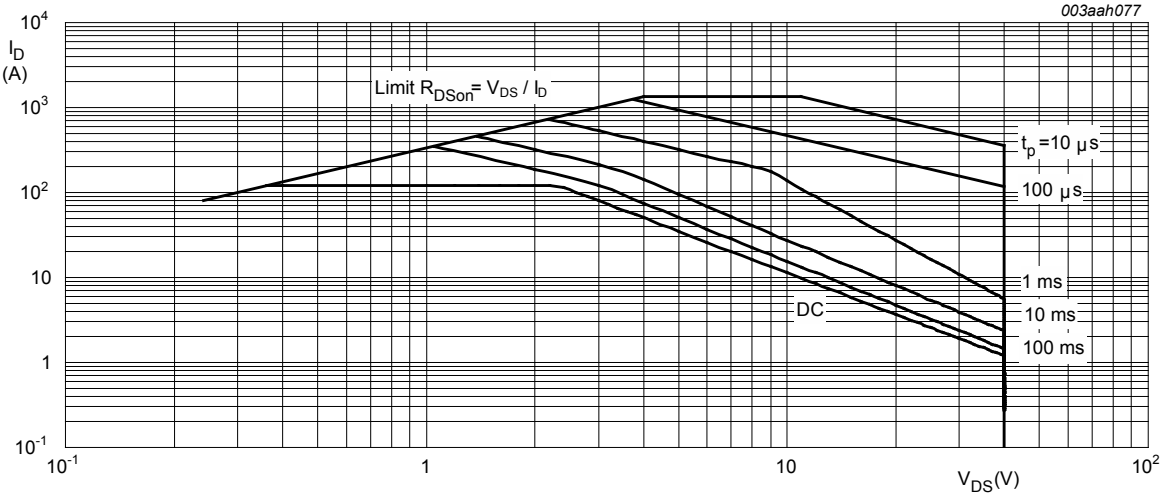


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}\text{C}$; I_{DM} is a single pulse

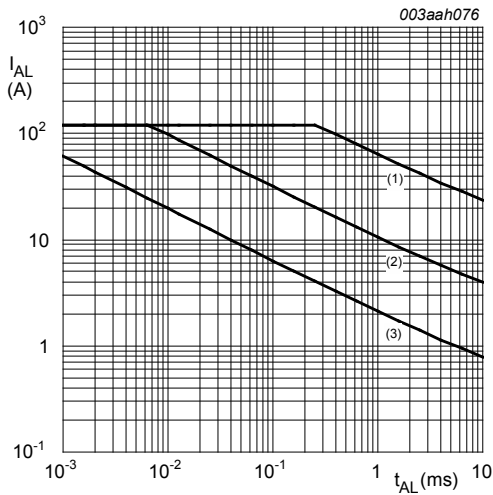


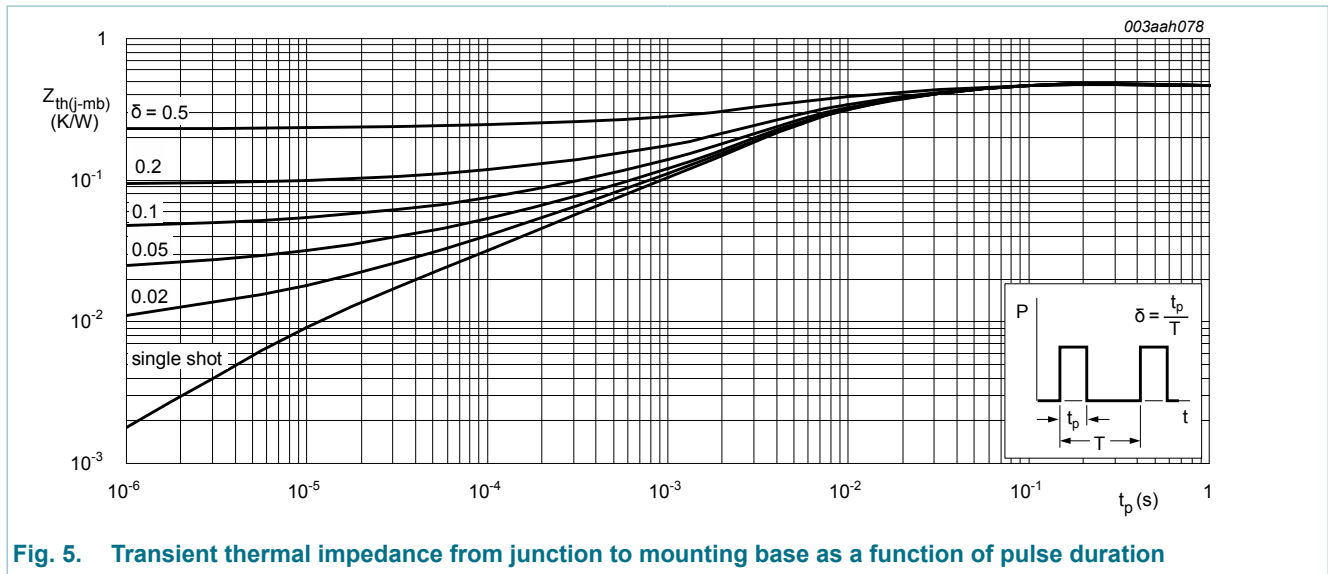
Fig. 4. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_j(\text{init}) = 25^{\circ}\text{C}$; (2) $T_j(\text{init}) = 150^{\circ}\text{C}$; (3) Repetitive Avalanche

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	0.46	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$		40	-	-	V
		$I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = -55\text{ }^\circ\text{C}$		36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}; V_{DS}=V_{GS}; T_j = 25\text{ }^\circ\text{C}$; Fig. 9 ; Fig. 10		2.4	3	4	V
		$I_D = 1\text{ mA}; V_{DS}=V_{GS}; T_j = -55\text{ }^\circ\text{C}$; Fig. 10		-	-	4.5	V
		$I_D = 1\text{ mA}; V_{DS}=V_{GS}; T_j = 175\text{ }^\circ\text{C}$; Fig. 10		1	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 40\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	0.27	3	μA
		$V_{DS} = 40\text{ V}; V_{GS} = 0\text{ V}; T_j = 175\text{ }^\circ\text{C}$		-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 20\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	2	100	nA
		$V_{GS} = -20\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 11		-	1.32	1.6	m Ω
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 175\text{ }^\circ\text{C}$; Fig. 12 ; Fig. 11		-	-	3	m Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 25\text{ A}; V_{DS} = 32\text{ V}; V_{GS} = 10\text{ V}$; Fig. 13 ; Fig. 14		-	118	-	nC
Q_{GS}	gate-source charge			-	29.3	-	nC
Q_{GD}	gate-drain charge			-	34.7	-	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C_{iss}	input capacitance	$V_{DS} = 25\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^{\circ}\text{C};$ Fig. 15		-	7873	10472	pF
C_{oss}	output capacitance			-	1410	1692	pF
C_{rss}	reverse transfer capacitance			-	851	1165	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30\text{ V}; R_L = 1.2\text{ }\Omega; V_{GS} = 10\text{ V};$ $R_{G(ext)} = 5\text{ }\Omega$		-	35	-	ns
t_r	rise time			-	49	-	ns
$t_{d(off)}$	turn-off delay time			-	87	-	ns
t_f	fall time			-	52	-	ns
L_D	internal drain inductance	from upper edge of drain mounting base to center of die		-	2.5	-	nH
L_S	internal source inductance	from source lead to source bonding pad		-	7.5	-	nH
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C};$ Fig. 16		-	0.79	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}; dI_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 25\text{ V}$		-	46	-	ns
Q_r	recovered charge			-	62	-	nC

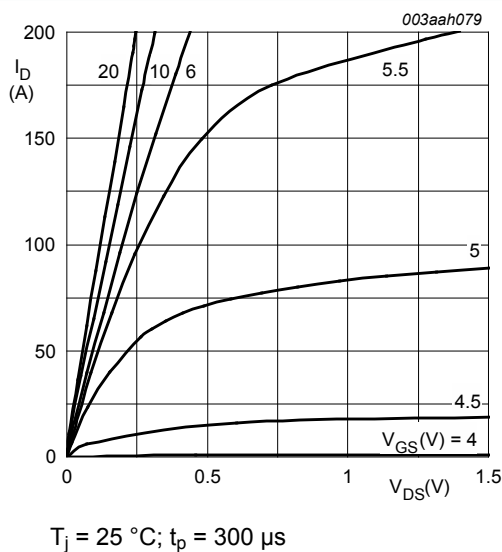


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

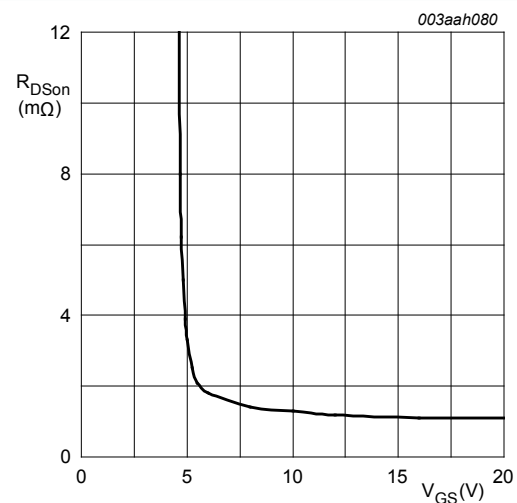


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^{\circ}\text{C}; I_D = 25\text{ A}$

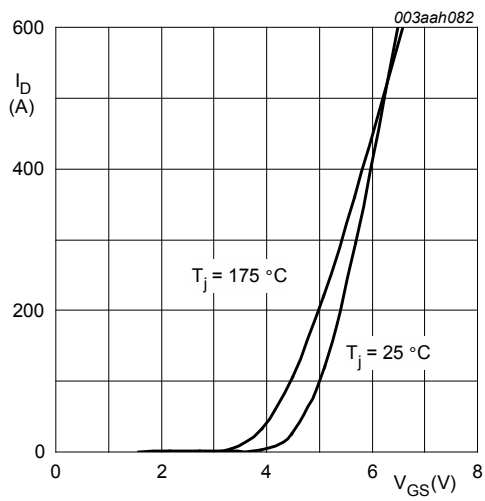


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{ V}$

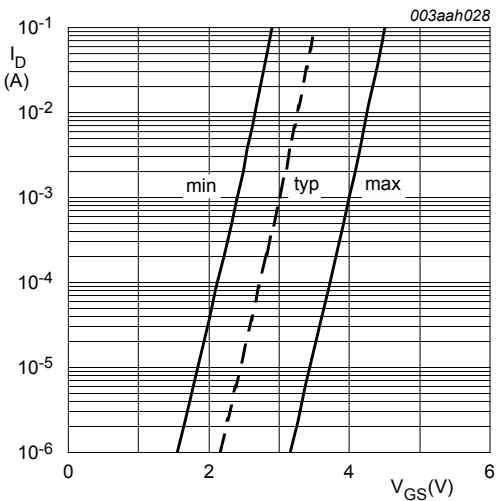


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$T_J = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

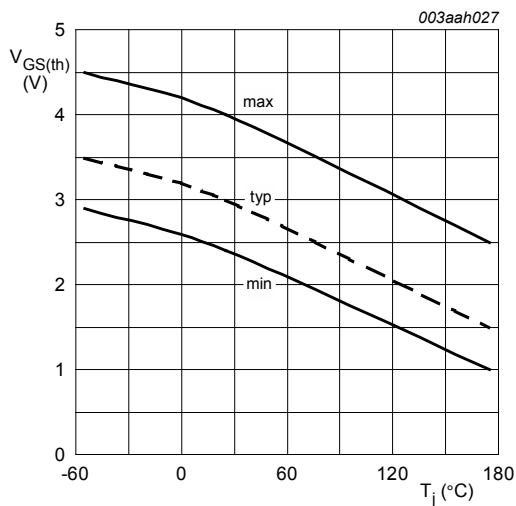


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

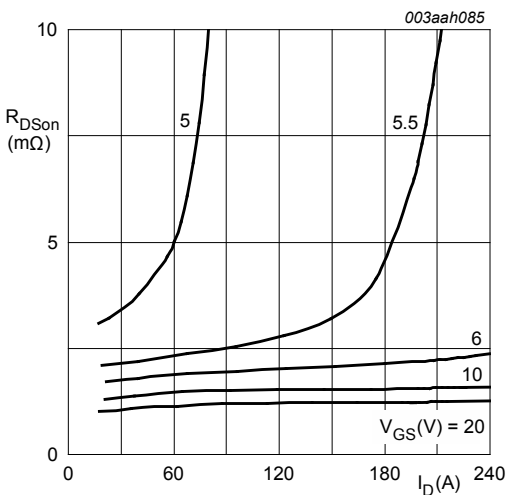


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_J = 25\text{ }^{\circ}\text{C}; t_p = 300\text{ }\mu\text{s}$

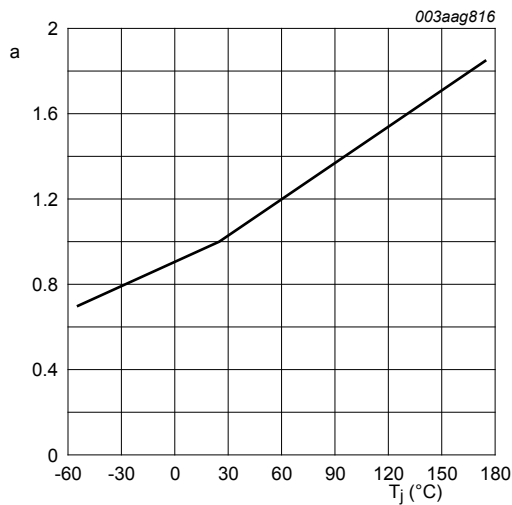


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

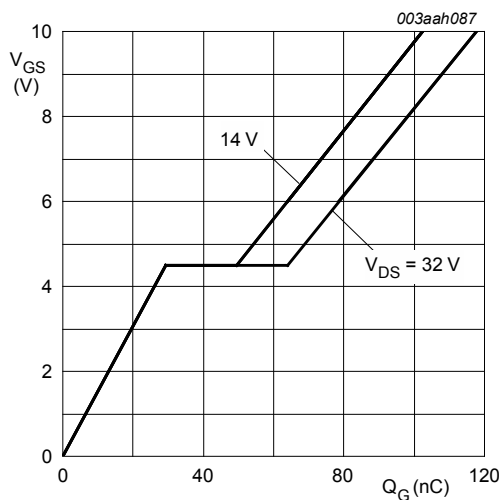


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}\text{C}; I_D = 25\text{A}$$

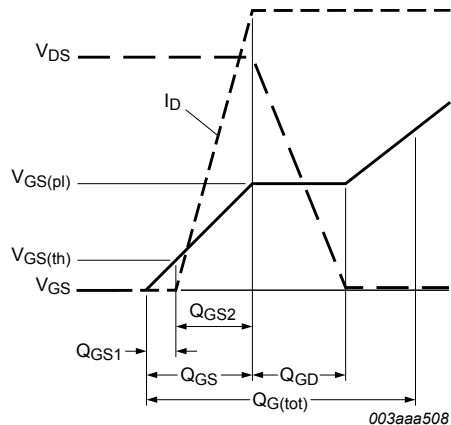


Fig. 13. Gate charge waveform definitions

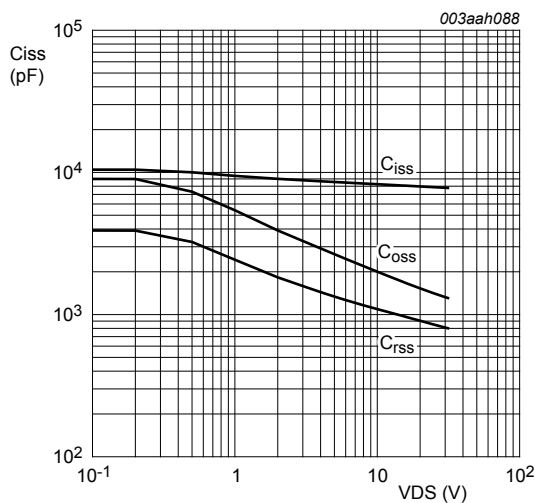


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

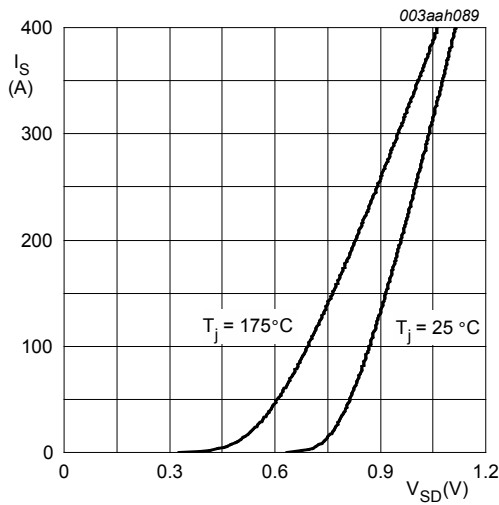


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values
 $V_{GS} = 0V$

11. Package outline

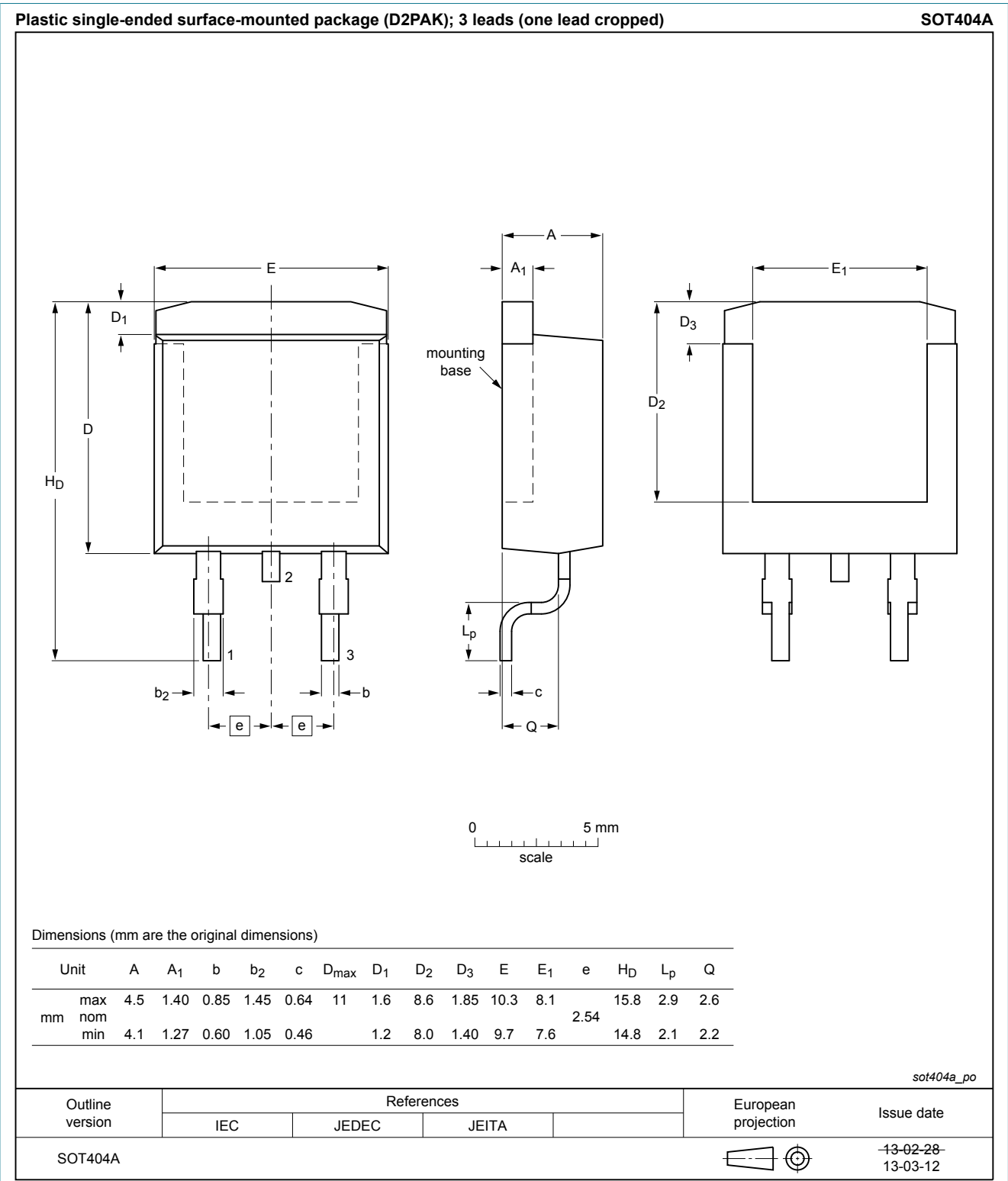


Fig. 17. Package outline D2PAK (SOT404A)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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